BOURNS®

- 12 A Continuous On-State Current
- 100 A Surge-Current
- Glass Passivated Wafer
- 400 V to 800 V Off-State Voltage
- Max I_{GT} of 20 mA

This series is obsolete and not recommended for new designs.

TO-220 PACKAGE (TOP VIEW) K 1 A 2 G 3

Pin 2 is in electrical contact with the mounting base.

MDC1ACA

absolute maximum ratings over operating case temperature (unless otherwise noted)

RATING			VALUE	UNIT
	TIC126D		400	
Repetitive peak off-state voltage	TIC126M	V	600	V
	TIC126S	V _{DRM}	700	
	TIC126N		800	
Repetitive peak reverse voltage	TIC126D		400	V
	TIC126M	V	600	
	TIC126S	V _{RRM}	700	
	TIC126N		800	
Continuous on-state current at (or below) 70°C case temperature (see Note 1)		I _{T(RMS)}	12	Α
Average on-state current (180° conduction angle) at (or below) 70°C case temperature			7.5	Α
(see Note 2)			7.5	^
Surge on-state current at (or below) 25°C case temperature (see Note 3)			100	Α
Peak positive gate current (pulse width ≤ 300 µs)		I _{GM}	3	Α
Peak gate power dissipation (pulse width ≤ 300 μs)		P _{GM}	5	W
Average gate power dissipation (see Note 4)		$P_{G(AV)}$	1	W
Operating case temperature range			-40 to +110	°C
Storage temperature range			-40 to +125	°C
Lead temperature 1.6 mm from case for 10 seconds		T _L	230	°C

- NOTES: 1. These values apply for continuous dc operation with resistive load. Above 70°C derate linearly to zero at 110°C.
 - 2. This value may be applied continuously under single phase 50 Hz half-sine-wave operation with resistive load. Above 70°C derate linearly to zero at 110°C.
 - 3. This value applies for one 50 Hz half-sine-wave when the device is operating at (or below) the rated value of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.
 - 4. This value applies for a maximum averaging time of 20 ms.



electrical characteristics at 25°C case temperature (unless otherwise noted)

	PARAMETER		TEST CONDITIO	ONS	MIN	TYP	MAX	UNIT
I _{DRM}	Repetitive peak off-state current	V _D = rated V _{DRM}		T _C = 110°C			2	mA
I _{RRM}	Repetitive peak reverse current	V _R = rated V _{RRM}	I _G = 0	T _C = 110°C			2	mA
I _{GT}	Gate trigger current	V _{AA} = 12 V	$R_L = 100 \Omega$	t _{p(g)} ≥ 20 μs		8	20	mA
V _{GT} Gate trigger voltage	$V_{AA} = 12 \text{ V}$ $t_{p(g)} \ge 20 \mu\text{s}$	$R_L = 100 \Omega$	T _C = - 40°C			2.5		
	Gate trigger voltage	$V_{AA} = 12 \text{ V}$ $t_{p(g)} \ge 20 \mu\text{s}$	$R_L = 100 \Omega$			0.8	1.5	٧
		$V_{AA} = 12 \text{ V}$ $t_{p(g)} \ge 20 \mu\text{s}$	$R_L = 100 \Omega$	T _C = 110°C	0.2			
I _H Holding current	$V_{AA} = 12 \text{ V}$ Initiating I _T = 100 mA		T _C = - 40°C			100	mA	
	riolaling durient	$V_{AA} = 12 \text{ V}$ Initiating $I_T = 100 \text{ mA}$					40	
V _T	On-state voltage	I _T = 12 A	(see Note 5)				1.4	V
dv/dt	Critical rate of rise of off-state voltage	V _D = rated V _D	I _G = 0	T _C = 110°C		400		V/µs

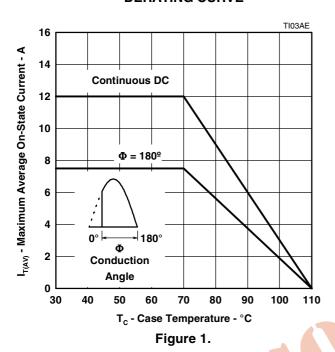
NOTE 5: This parameter must be measured using pulse techniques, t_p = 300 µs, duty cycle ≤ 2 %. Voltage sensing-contacts, separate from the current carrying contacts, are located within 3.2 mm from the device body.

thermal characteristics

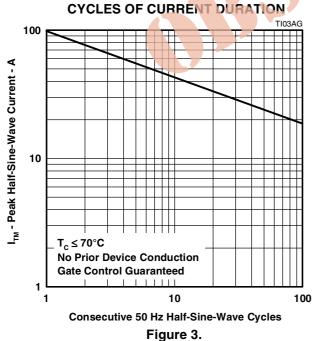
PARAMETER	MIN	TYP	MAX	UNIT
R _{0JC} Junction to case thermal resistance			2.4	°C/W
R _{eJA} Junction to free air thermal resistance			62.5	°C/W

THERMAL INFORMATION

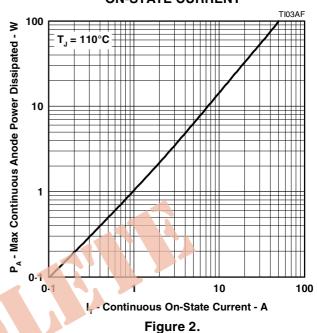
AVERAGE ON-STATE CURRENT DERATING CURVE



SURGE ON-STATE CURRENT vs

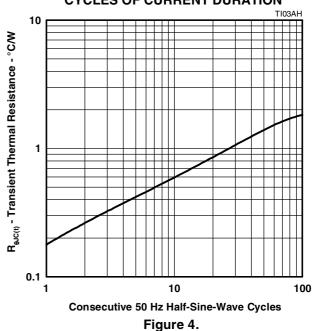


MAX ANODE POWER LOSS vs ON-STATE CURRENT



TRANSIENT THERMAL RESISTANCE vs

CYCLES OF CURRENT DURATION



TYPICAL CHARACTERISTICS

GATE TRIGGER CURRENT vs

CASE TEMPERATURE

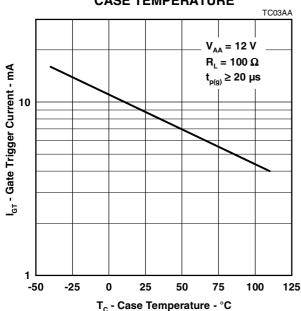


Figure 5.

HOLDING CURRENT vs

CASE TEMPERATURE

TC03AD

V_™ - Peak On-State Voltage - V

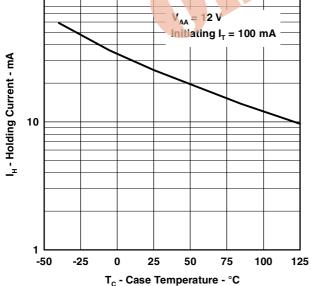


Figure 7.

GATE TRIGGER VOLTAGE vs

CASE TEMPERATURE

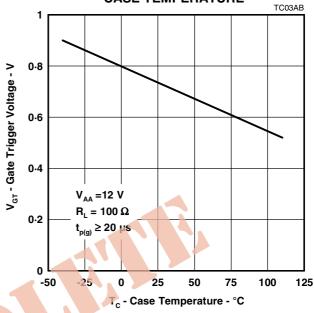
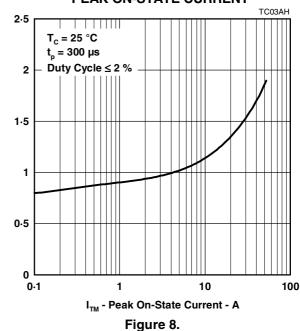


Figure 6.

PEAK ON-STATE VOLTAGE

PEAK ON-STATE CURRENT



100